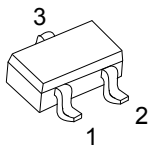
UT1D5P06

Power MOSFET

-1.5A, -60V P-CHANNEL POWER MOSFET



SOT-23
(EIAJ SC-59)

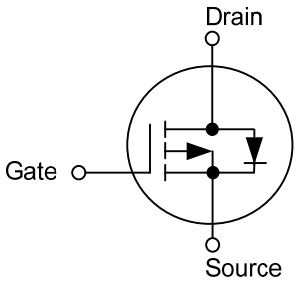
■ DESCRIPTION

The UTC **UT1D5P06** is a P-channel enhancement power MOSFET using UTC's advanced technology to provide the customers with perfect $R_{DS(ON)}$ and low gate charge.

■ FEATURES

* $R_{DS(ON)} \leq 0.23\ \Omega$ @ V_{GS}= -10V, I_D= -0.9A
  $R_{DS(ON)} \leq 0.27\ \Omega$ @ V_{GS}= -4.5V, I_D= -0.8A
* High switching speed

■ SYMBOL



■ ORDERING INFORMATION

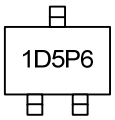
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
UT1D5P06L-AE3-R	UT1D5P06G-AE3-R	SOT-23	G	S	D	Tape Reel

Note: Pin Assignment: G: Gate S: Source D: Drain

UT1D5P06G-AE3-R

(1)Packing Type	(1) R: Tape Reel
(2)Package Type	(2) AE3: SOT-23
(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free

■ MARKING



■ ABSOLUTE MAXIMUM RATINGS (T_C=25°C, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	-60	V
Gate-Source Voltage		V_{GSS}	±20	V
Continuous Drain Current	Continuous	I_D	-1.5	A
Pulsed Drain Current	Pulsed (Note 2)	I_{DM}	-3.0	A
Single Pulsed Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	6.5	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.7	V/ns
Power Dissipation		P_D	0.35	W
Junction Temperature		T_J	+150	°C
Storage Temperature		T_{STG}	-55 ~ +150	°C

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.
2. Repetitive Rating: Pulse width limited by maximum junction temperature.
3. L=0.1mH, I_{AS}=-11A, V_{DD}=-50V, R_G=25Ω, Starting T_J=25°C
4. I_{SD}≤-1.5A, di/dt ≤ 200μA/ s, V_{DD}≤BV_{DSS}, Starting T_J=25°C

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Junction to Case	θ_{JC}	357	°C/W

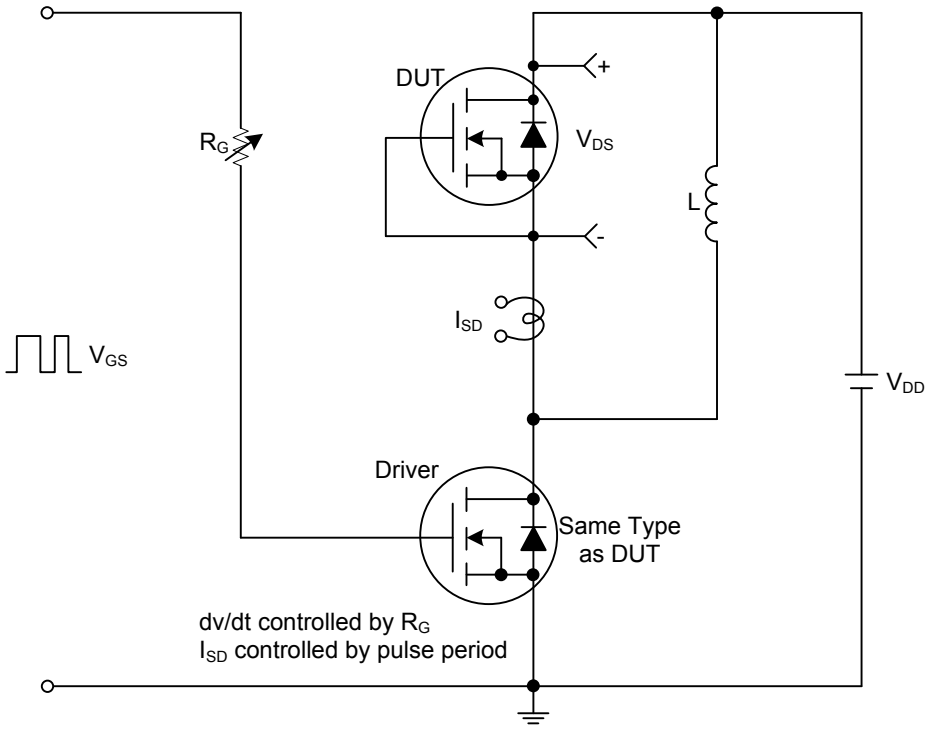
Note: Device mounted on FR-4 substrate P_C board, 2oz copper, with 1inch square copper plate.

■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

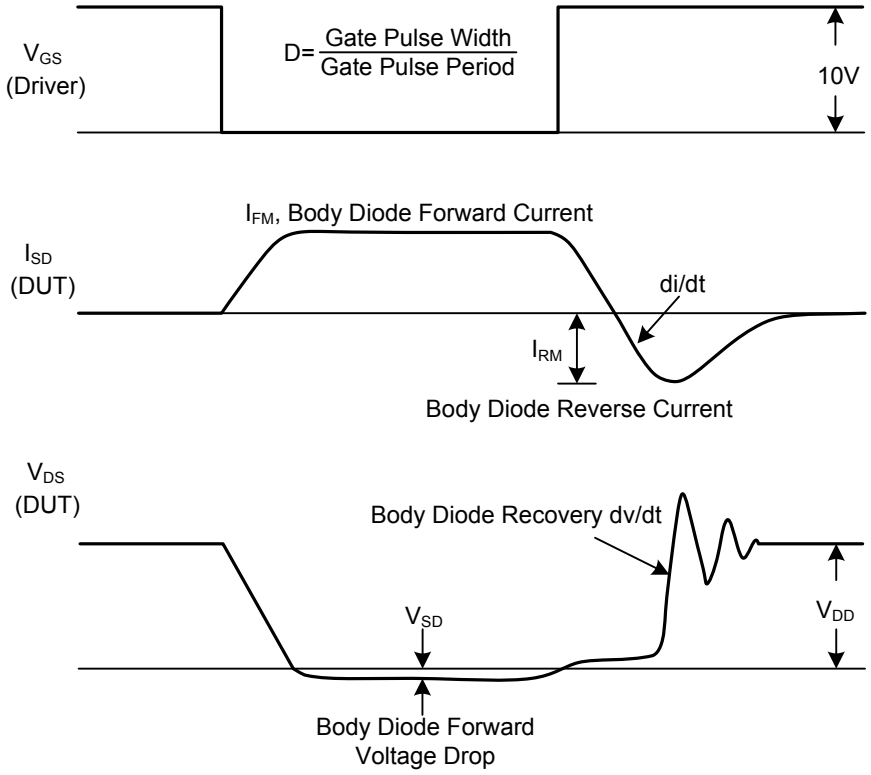
PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV_{DSS}	V_{GS}=0 V, I_D=-250μA	-60			V
Drain-Source Leakage Current		I_{DSS}	V_{DS}=-60V, V_{GS}=0V			-1	μA
Gate-Source Leakage Current	Forward	I_{GSS}	V_{DS}=0V, V_{GS}=+20V			100	nA
	Reverse		V_{DS}=0V, V_{GS}=-20V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		$V_{GS(TH)}$	V_{DS}=V_{GS}, I_D=-250μA	-1.0		-3.0	V
Static Drain-Source On-Resistance		$R_{DS(ON)}$	V_{GS}=-10V, I_D=-0.9A			0.23	Ω
			V_{GS}=-4.5V, I_D=-0.8A			0.27	Ω
DYNAMIC PARAMETERS							
Input Capacitance		C_{ISS}	V_{DS}=-25V, V_{GS}=0V, f=1.0MHz		350		pF
Output Capacitance		C_{OSS}			32		pF
Reverse Transfer Capacitance		C_{RSS}			22		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q_G	V_{DS}=-48V, V_{GS}=-10V, I_D=-1.5A (Note 1, 2)		13		nC
Gate Source Charge		Q_{GS}			3		nC
Gate Drain Charge		Q_{GD}			1.5		nC
Turn-ON Delay Time (Note 1)		$t_{D(ON)}$	V_{DD}=-30V, V_{GS}=-10V, I_D=-1.5A, R_G=3Ω (Note 1, 2)		4		ns
Turn-ON Rise Time		t_R			17		ns
Turn-OFF Delay Time		$t_{D(OFF)}$			19		ns
Turn-OFF Fall-Time		t_F			17		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I_S				1.5	A
Maximum Pulsed Drain-Source Diode Forward Current		I_{SM}				3	A
Diode Forward Voltage (Note 1)		V_{SD}	I_S=-1.5A, V_{GS}=0V			1.4	V
Body Diode Reverse Recovery Time(Note 1)		t_{rr}	I_S=-1.5A, V_{GS}=0V, dI_F/dt=100A/μs		16		ns
Body Diode Reverse Recovery Charge		Q_{rr}			12		nC

Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle≤2%.
2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



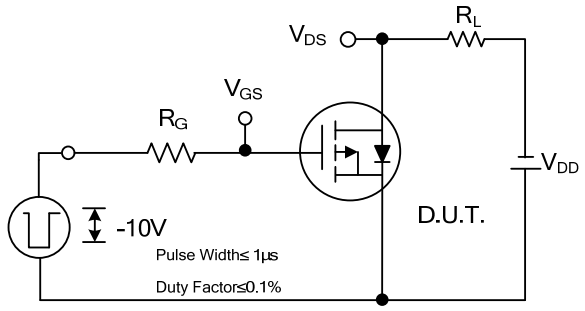
Peak Diode Recovery dv/dt Test Circuit



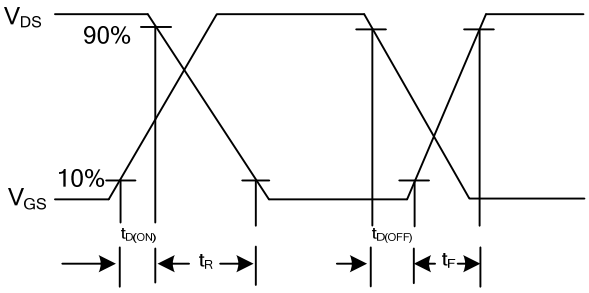
Peak Diode Recovery dv/dt Test Circuit and Waveforms

Peak Diode Recovery dv/dt Waveforms

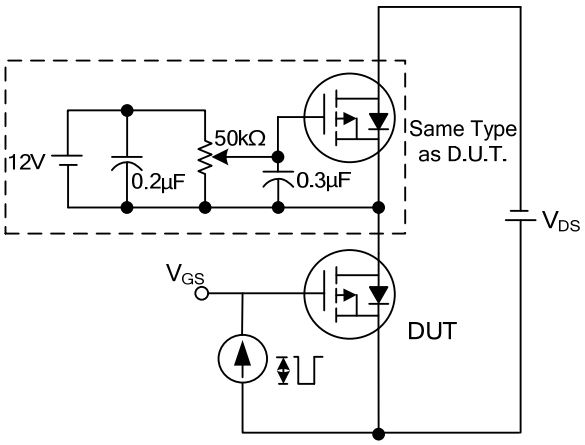
■ TEST CIRCUITS AND WAVEFORMS



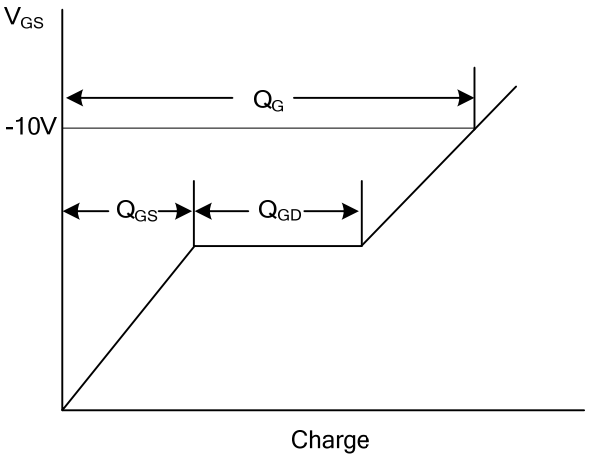
Switching Test Circuit



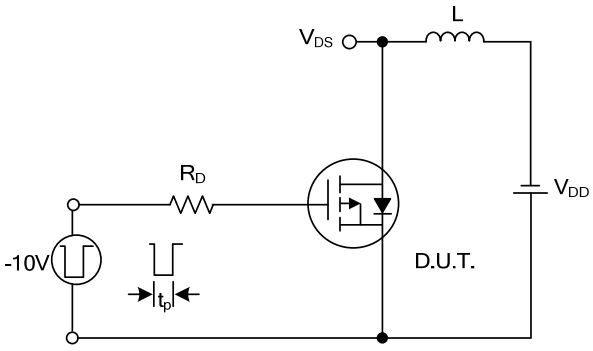
Switching Waveforms



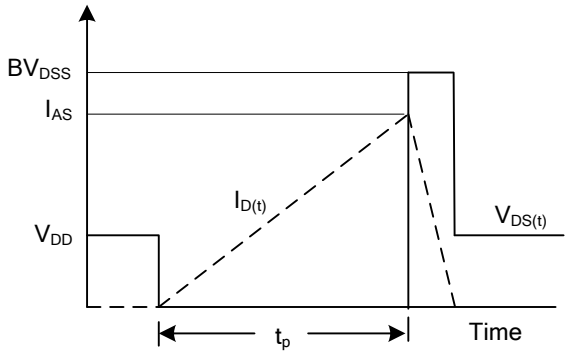
Gate Charge Test Circuit



Gate Charge Waveform



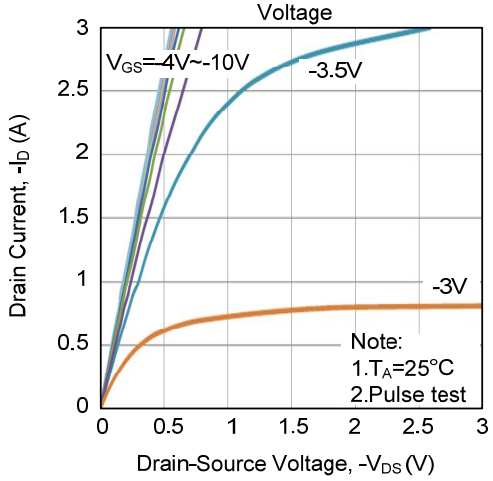
Unclamped Inductive Switching Test Circuit



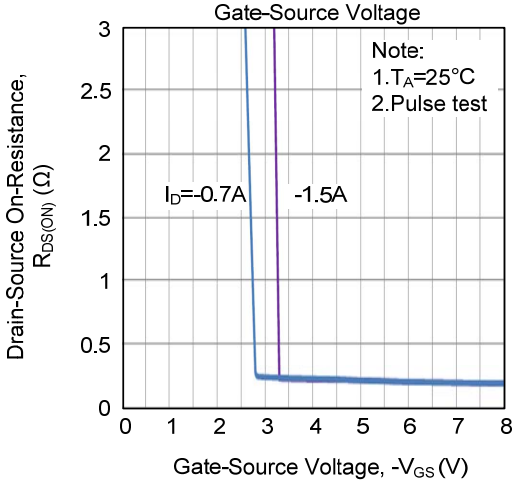
Unclamped Inductive Switching Waveforms

■ TYPICAL CHARACTERISTICS

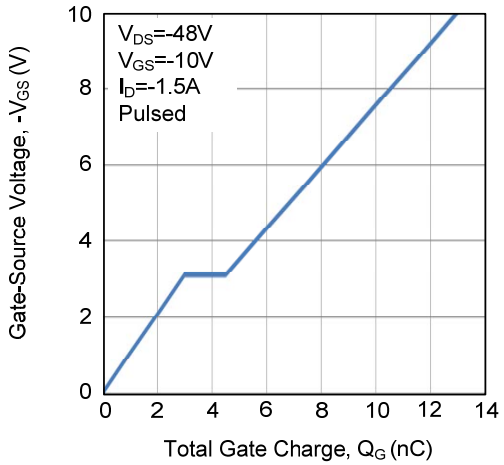
Drain Current vs. Drain-Source Voltage



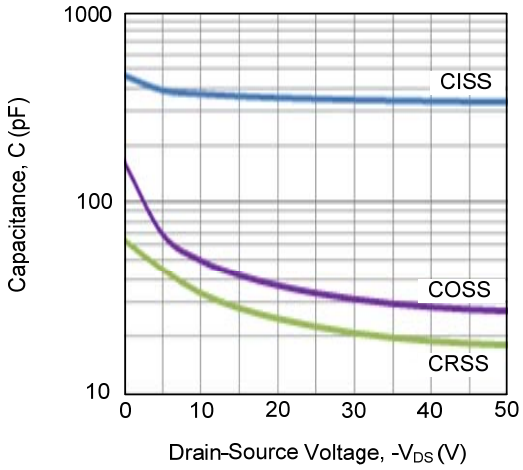
Drain-Source On-Resistance vs. Gate-Source Voltage



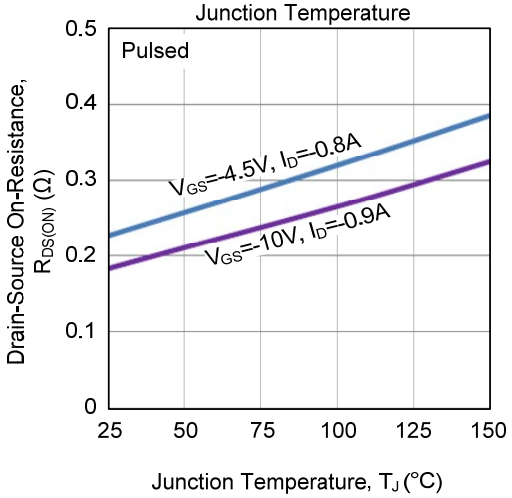
Gate Charge Characteristics



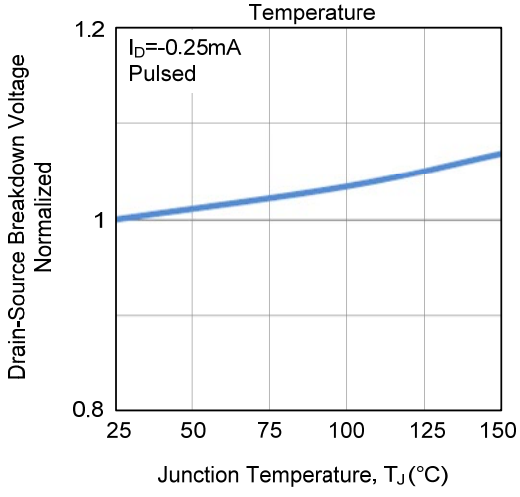
Capacitance Characteristics



Drain-Source On-Resistance vs. Junction Temperature

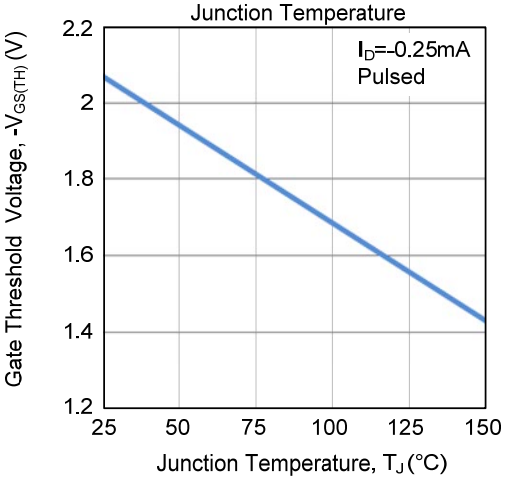


Breakdown Voltage vs. Junction Temperature

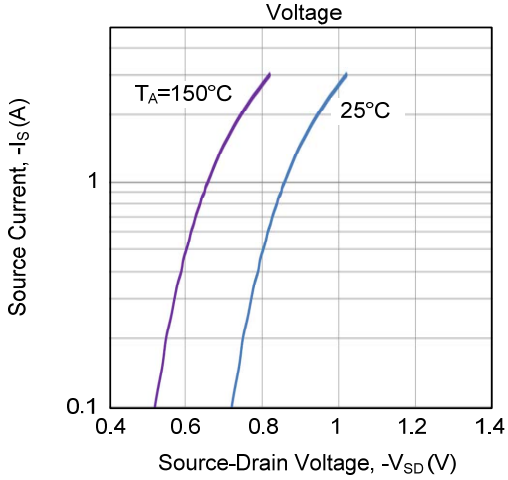


■ TYPICAL CHARACTERISTICS (Cont.)

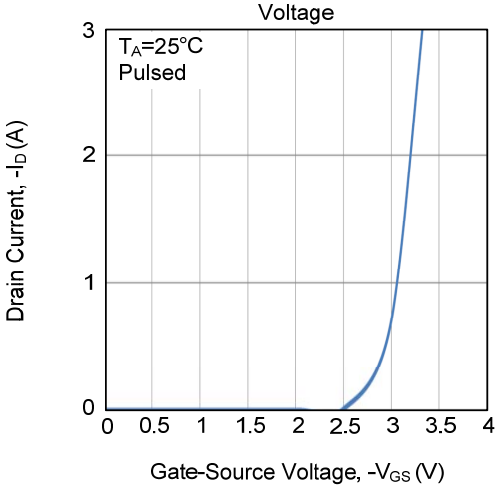
Gate Threshold Voltage vs. Junction Temperature



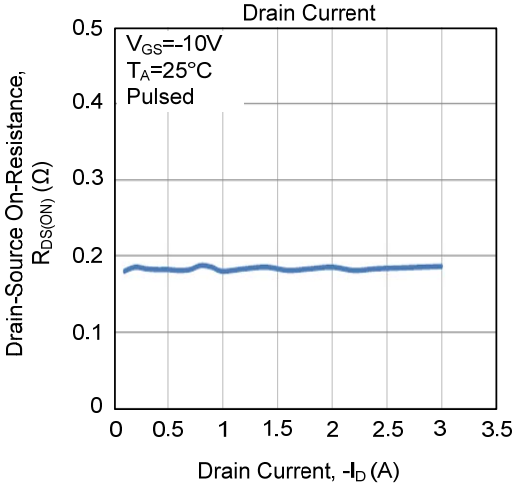
Source Current vs. Source-Drain Voltage



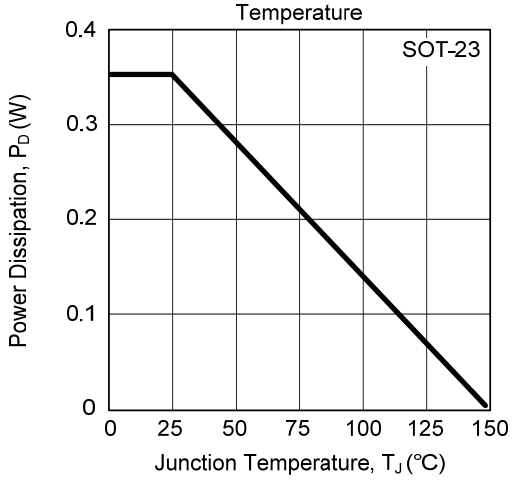
Drain Current vs. Gate-Source Voltage



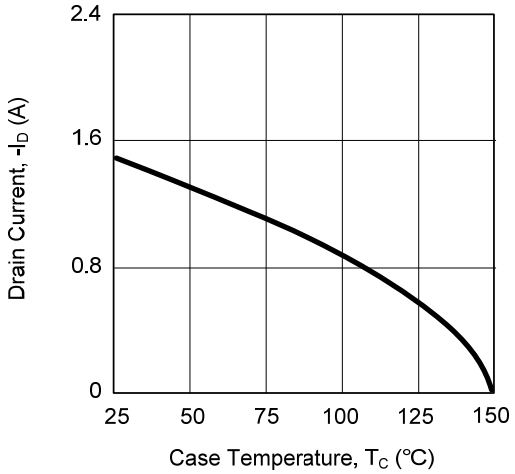
Drain-Source On-Resistance vs. Drain Current



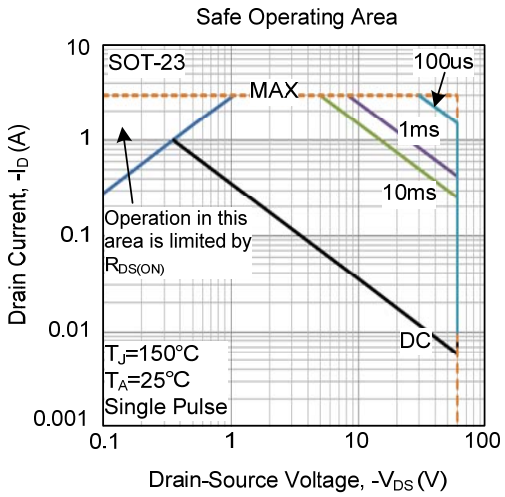
Power Dissipation vs. Junction Temperature



Drain Current vs. Case Temperature



■ TYPICAL CHARACTERISTICS (Cont.)



Note: 250°C/W when mounted on a 0.02 in2 pad of 2 oz. copper.